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Inclosure Material:	
Metal	
Overall Length:	
0.180 inches	
Terminal Length:	
1.500 inches	
Overall Diameter:	
0.335 inches	
Joint Electronic Devi	ce Engineering Council/jedec/case Outline Designation:
То-5	
Electrode Internally-e	ectrically Connected To Case:
Collector	
Component Name An	d Quantity:
2 transistor	
Mounting Method:	
Terminal	
Terminal Circle Diam	eter:
0.200 inches	
Features Provided:	
Hermetically sealed ca	se
Semiconductor Mater	ial:
Silicon all transistor	
Voltage Rating In Vol	ts Per Characteristic:
60.0 breakdown voltag	ge, collector-to-base, emitter open all transistor and 30.0 breakdown voltage, collector-to-emitter, base open all
transistor and 5.0 emit	tter to base voltage, static, collector open all transistor
Current Rating Per C	haracteristic:
800.00 milliamperes so	purce cutoff current all transistor
Power Rating Per Cha	aracteristic:
800.0 milliwatts small-s	signal input power, common-collector absolute all transistor
Transfer Ratio:	
25.0 small-signal shor	t-circuit forward current transfer ratio, common-emitter all transistor
Maximum Operating	Tempurature Per Measurement Point:
200.0 degrees celsius	junction
Special Features:	
Internal junction config	uration transistor npn
Terminal Type And Q	uantity:
6 uninsulated wire lead	I
Shelf Life:	
N/a	
Unit Of Measure:	

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